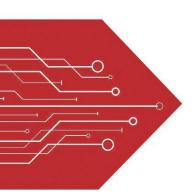
# MSKSEMI















**ESD** 

**TVS** 

**TSS** 

MOV

**GDT** 

**PLED** 

Broduct data speet



Semiconductor



For use in low voltage, high frequency inverters Free wheeling, and polarity protection applications

**SOD-323** 



MARKING: B5817WS-MS: SJ

B5818WS-MS:SK

B5819WS-MS: SL



## Maximum Ratings and Electrical Characteristics, Single Diode @Ta=25℃

Parameter	Symbol	B5817WS-MS	B5818WS-MS	B5819WS-MS	Unit
Non-repetitive peak reverse voltage	V <sub>RM</sub>	20	30	40	V
Peak repetitive peak reverse voltage Working peak reverse voltage DC blocking voltage	V <sub>RRM</sub> V <sub>RWM</sub> V <sub>R</sub>	20	30	40	V
RMS reverse voltage	V <sub>R(RMS)</sub>	14	21	28	V
Average rectified output current	Io	1			Α
Peak forward surge current @t=8.3ms	I <sub>FSM</sub>	9		Α	
Repetitive peak forward current	I <sub>FRM</sub>	1.5		Α	
Power dissipation	Pd	250		mW	
Thermal resistance junction to ambient	R <sub>θJA</sub>	400		°C/W	
Junction temperature	TJ	125		${}^{\sim}$	
Storage temperature	T <sub>STG</sub>	-55~+150			$^{\circ}$

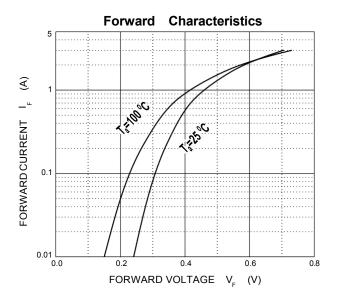
## **ELECTRICAL CHARACTERISTICS (Ta=25℃ unless otherwise specified)**

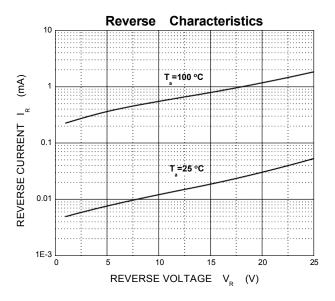
Parameter	Symbol	Test conditions	Min	Max	Unit
Reverse breakdown voltage	V <sub>(BR)</sub>	I <sub>R</sub> = 1mA B5817WS-MS B5818WS-MS B5819WS-MS	30		V
Reverse voltage leakage current	I <sub>R</sub>	V <sub>R</sub> =20V B5817WS-MS V <sub>R</sub> =30V B5818WS-MS V <sub>R</sub> =40V B5819WS-MS		1	mA
	VF	B5817WS-MS I <sub>F</sub> =1A I <sub>F</sub> =3A		0.45 0.75	V
Forward voltage		B5818WS-MS I <sub>F</sub> =1A I <sub>F</sub> =3A		0.55 0.875	V
		B5819WS-MS I <sub>F</sub> =1A I <sub>F</sub> =3A		0.6 0.9	V
Diode capacitance	C <sub>D</sub>	V <sub>R</sub> =4V, f=1MHz		120	pF

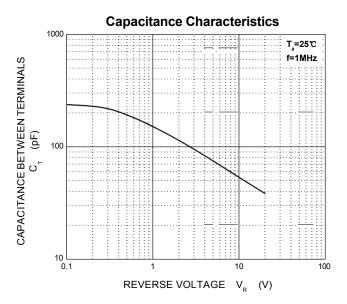


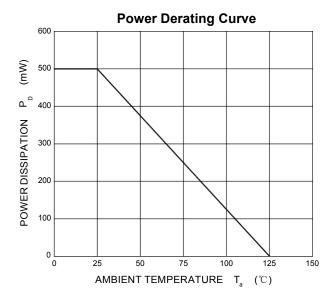








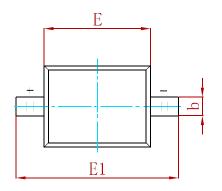


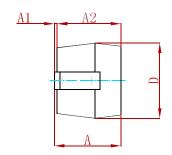


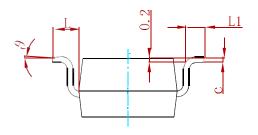




# **PACKAGE MECHANICAL DATA**

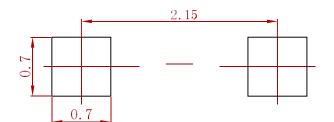






Cumbal	Dimensions	In Millimeters	Dimensions In Inches		
Symbol	Min.	Max.	Min.	Max.	
Α		1.000		0.039	
A 1	0.000	0.100	0.000	0.004	
A2	0.800	0.900	0.031	0.035	
b	0.250	0.350	0.010	0.014	
С	0.080	0.150	0.003	0.006	
D	1.200	1.400	0.047	0.055	
E	1.600	1.800	0.063	0.071	
E1	2.550	2.750	0.100	0.108	
L	0.475	REF.	0.019 REF.		
L1	0.250	0.400	0.010	0.016	
θ	0°	8°	0°	8°	

# **Suggested Pad Layout**



#### Note:

- 1. Controlling dimension: in millimeters.
- 2.General tolerance:± 0.05mm.
- 3. The pad layout is for reference purposes only.

## **REEL SPECIFICATION**

P/N	PKG	QTY
B5817WS-MS	SOD-323	3000
B5818WS-MS	SOD-323	3000
B5819WS-MS	SOD-323	3000



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